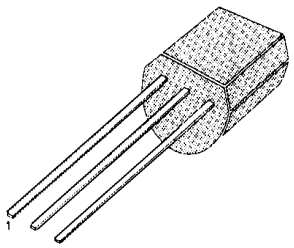
KSP05/06 PNP EPITAXIAL SILICON TRANSISTOR

AMPLIFIER TRANSITOR

- Collector-Emitter Voltage: V_{CEO} = KSP05: 60V
  KSP06: 80V
- Collector Dissipation: PC(max)=625mW

TO-92



1. Emitter 2. Base 3. Collector

ABSOLUTE MAXIMUM RATINGS (T_A=25℃)

Characteristic	Symbol	Rating	Unit
Collector Base Voltage	V_{CBO}		
:KSP05		60	V
:KSP06		80	V
Collector-Emitter Voltage	V_{CEO}		
:KST05		60	V
:KST06		80	V
Emitter-Base Voltage	V_{EBO}	4	V
Collector Current	I_C	500	mA
Collector Dissipation	P_C	625	mW
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55~150	℃

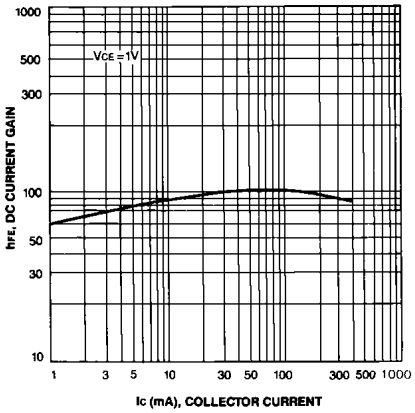
ELECTRICAL CHARACTERISTICS (T_A=25℃)

Characteristic	Symbol	Test Conditions	Min	Max	Unit
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=1mA, I_B=0			
:KSP05			60		V
:KSP06			80		V
Collector-Base Breakdown Voltage	BV_{EBO}	I_E=100㎂, I_C=0	4		V
Collector Cut-off Current	I_{CBO}				
:KSP05		V_{CB}=60V, I_E=0		0.1	㎂
:KSP06		V_{CB}=80V, I_E=0		0.1	㎂
Collector Cut-off Current	I_{CEO}	V_{CE}=60V, I_B=0V		0.1	㎂
DC Current Gain	h_{FE}	V_{CE}=1V, I_C=10mA	50		
		V_{CE}=1V, I_C=100mA	50		
Collector-Emitter Saturation Voltage	V_{CE} (sat)	I_C=100mA, I_B=10mA		0.25	V
Base-Emitter On Voltage	V_{BE} (sat)	V_{CE}=1V, I_C=100mA		1.2	V
Current Gain Bandwidth Product	f_T	V_{CE}=2V, I_C=10mA f=100MHz	100		MHz

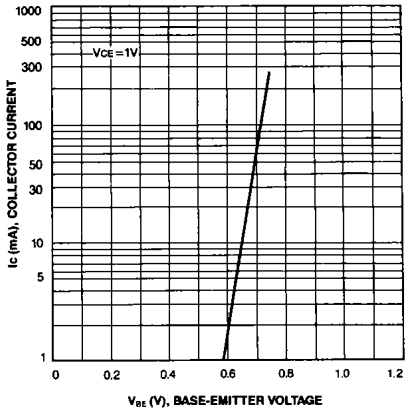
★Pulse Test: PW ≤ 300㎲, Duty Cycle ≤ 2%

SAMSUNG ELECTRONICS

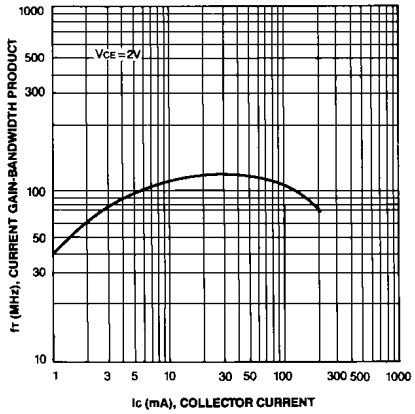
DC CURRENT GAIN



BASE-EMITTER ON VOLTAGE



CURRENT GAIN-BANDWIDTH PRODUCT



COLLECTOR-EMITTER SATURATION VOLTAGE
BASE-EMITTER SATURATION VOLTAGE